74AHC273-Q100; 74AHCT273-Q100

Octal D-type flip-flop with reset; positive-edge trigger

Rev. 1 — 27 March 2013

Product data sheet

1. General description

The 74AHC273-Q100; 74AHCT273-Q100 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7-A.

The 74AHC273-Q100; 74AHCT273-Q100 has eight edge-triggered, D-type flip-flops with individual D inputs and Q outputs.

The common clock (CP) and master reset (\overline{MR}) inputs, load and reset (clear) all flip-flops simultaneously. The state of each D input, one set-up time before the LOW-to-HIGH clock transition, is transferred to the corresponding output (Qn) of the flip-flop.

All outputs are forced LOW, independent of clock or data inputs, by a LOW on the $\overline{\text{MR}}$ input.

The device is useful for applications where only the true output is required and the clock and master reset are common to all storage elements.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Balanced propagation delays
- All inputs have Schmitt-trigger actions
- Inputs accept voltages higher than V_{CC}
- Ideal buffer for MOS microcontroller or memory
- Common clock and master reset
- Input levels:
 - ◆ For 74AHC273-Q100: CMOS level
 - For 74AHCT273-Q100: TTL level
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - ♦ HBM JESD22-A114F exceeds 2000 V
 - ♦ MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

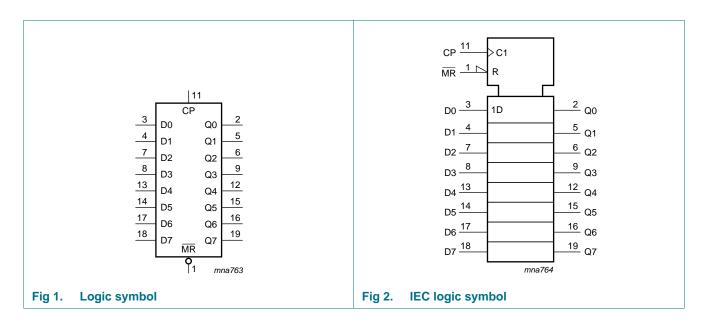


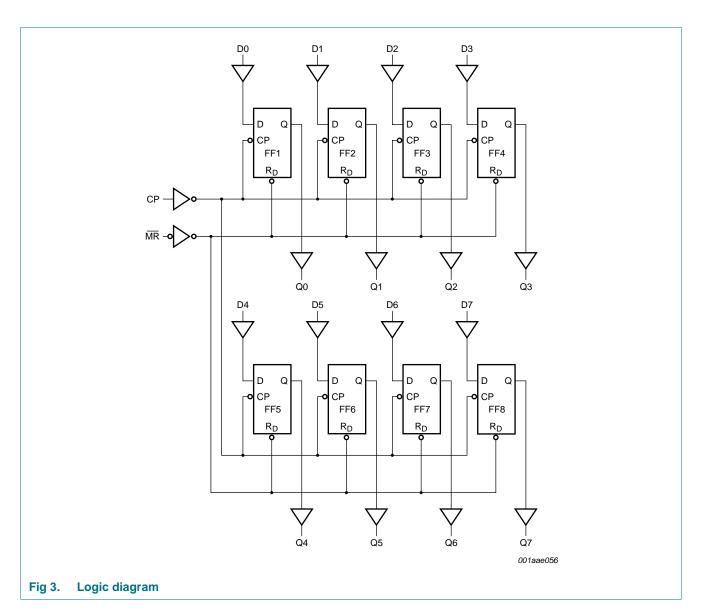
3. Ordering information

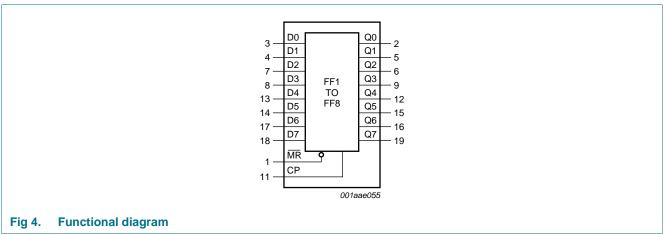
Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC273-Q100		'		•
74AHC273D-Q100	–40 °C to +125 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74AHC273PW-Q100	–40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74AHC273BQ-Q100	–40 °C to +125 °C	DHVQFN20	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body $2.5 \times 4.5 \times 0.85$ mm	SOT764-1
74AHCT273-Q100				
74AHCT273D-Q100	–40 °C to +125 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74AHCT273PW-Q100	–40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74AHCT273BQ-Q100	–40 °C to +125 °C	DHVQFN20	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body $2.5 \times 4.5 \times 0.85$ mm	SOT764-1

4. Functional diagram

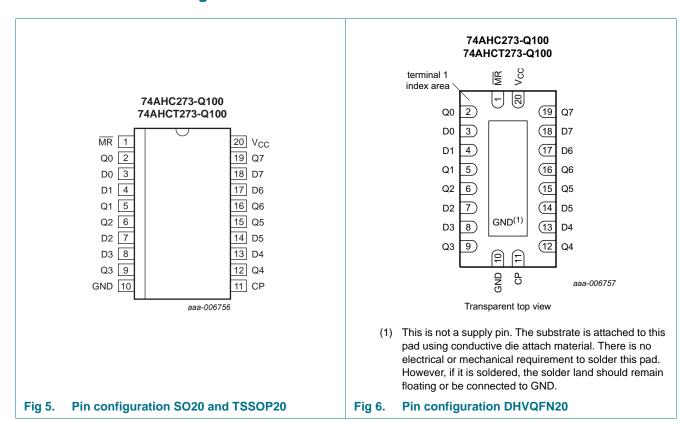






5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
MR	1	master reset input (active LOW)
Q0, Q1, Q2, Q3, Q4, Q5, Q6, Q7	2, 5, 6, 9, 12, 15, 16, 19	flip-flop output
D0, D1, D2, D3, D4, D5, D6, D7	3, 4, 7, 8, 13, 14, 17, 18	data input
GND	10	ground (0 V)
СР	11	clock input (LOW-to-HIGH edge-triggered)
V _{CC}	20	supply voltage

6. Functional description

Table 3. Function table[1]

Operating mode	Control	Control		Output
	MR	СР	Dn	Qn
Reset (clear)	L	X	X	L
Load '1'	Н	↑	h	Н
Load '0'	Н	↑	I	L

^[1] H = HIGH voltage level;

h = HIGH voltage level one set-up time prior to the LOW-to-HIGH CP transition;

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

	Max	Unit
$\begin{array}{cccccccccccccccccccccccccccccccccccc$.70	
I_{IK} input clamping current $V_I < -0.5 \text{ V}$ [1] -20 I_{OK} output clamping current $V_O < -0.5 \text{ V}$ or $V_O > V_{CC} + 0.5 \text{ V}$ [1] -20	+7.0	V
I_{OK} output clamping current $V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$ [1] -20	+7.0	V
	-	mA
$V_{\rm O} = -0.5 \text{ V} \text{ to } (V_{\rm CC} + 0.5 \text{ V})$ -25	+20	mA
	+25	mA
I _{CC} supply current -	+75	mA
I _{GND} ground current -75	-	mA
T _{stg} storage temperature –65	+150	°C
P_{tot} total power dissipation $T_{amb} = -40 ^{\circ}\text{C}$ to +125 $^{\circ}\text{C}$	500	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

L = LOW voltage level;

I = LOW voltage level one set-up time prior to the LOW-to-HIGH CP transition;

 $[\]uparrow$ = LOW-to-HIGH;

X = don't care.

^[2] For SO20 packages: above 70 $^{\circ}\text{C}$ the value of Ptot derates linearly at 8 mW/K.

For TSSOP20 packages: above 60 $^{\circ}\text{C}$ the value of Ptot derates linearly at 5.5 mW/K.

For DHVQFN20 packages: above 60 $^{\circ}$ C the value of P_{tot} derates linearly at 4.5 mW/K.

8. Recommended operating conditions

Table 5. Operating conditions

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
74AHC273	-Q100					
V_{CC}	supply voltage		2.0	5.0	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage		0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	100	ns/V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	20	ns/V
74AHCT27	'3-Q100					
V _{CC}	supply voltage		4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	20	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol Parameter		Conditions		25 °C		-40 °C 1	o +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
74AHC2	73-Q100		•			'				'
V_{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V _{IL}	LOW-level	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V _{OH} HIGH-level	$V_I = V_{IH}$ or V_{IL}									
	output voltage	$I_O = -50 \mu A$; $V_{CC} = 2.0 \text{ V}$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -50 \mu A; V_{CC} = 3.0 \text{ V}$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_O = -50 \mu A$; $V_{CC} = 4.5 \text{ V}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_{O} = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.80	-	3.70	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = 50 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 3.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	٧
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
		I_{O} = 8.0 mA; V_{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V

74AHC_AHCT273_Q100

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 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C	to +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
II	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	4.0	-	40	-	80	μА
Cı	input capacitance		-	3	10	-	10	-	10	pF
C _O	output capacitance		-	4	-	-	-	-	-	pF
74AHCT	273-Q100									
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	-	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	8.0	-	0.8	-	0.8	V
V _{OH} HIGH-level		$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_{O} = -50 \ \mu A$	4.4	-	-	4.4	-	4.4	-	V
		$I_{O} = -8.0 \text{ mA}$	3.94	-	-	3.80	-	3.70	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_{O} = 50 \mu A$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 8.0 \text{ mA}$	-	-	0.36	-	0.44	-	0.55	V
I _I	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to 5.5 V}$	-	-	0.1	-	1.0	-	2.0	μА
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	4.0	-	40	-	80	μА
Δl _{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}$; other pins at V_{CC} or GND; $I_O = 0 \text{ A}$; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
Cı	input capacitance		-	3	10	-	10	-	10	pF
C _O	output capacitance		-	4	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 10.

Symbol	Parameter	Conditions		25 °C		-40 °C to +85 °C		-40 °C to +125 °C		Unit	
				Min	Typ[1]	Max	Min	Max	Min	Max	
74AHC2	73-Q100	'				'				'	
t _{pd}	propagation	CP to Qn; see Figure 7	[2]								
	delay	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$									
		C _L = 15 pF		-	6.0	13.6	1.0	16.0	1.0	17.0	ns
		$C_L = 50 pF$		-	8.6	17.1	1.0	19.5	1.0	21.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$									
		C _L = 15 pF		-	4.2	9	1.0	10.5	1.0	11.5	ns
		$C_L = 50 pF$		-	6.0	11.0	1.0	12.5	1.0	14.0	ns
		MR to Qn; see Figure 8	[3]								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$									
		C _L = 15 pF		-	5.1	13.6	1.0	16.0	1.0	17.0	ns
		$C_L = 50 pF$		-	7.3	17.1	1.0	19.5	1.0	21.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$									
		C _L = 15 pF		-	3.7	8.5	1.0	10.0	1.0	11.0	ns
		$C_L = 50 pF$		-	5.3	10.5	1.0	12.0	1.0	13.5	ns
f _{max} maximum frequency	maximum	see Figure 7									
	frequency	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$									
		C _L = 15 pF		75	120	-	65	-	65	-	MHz
		$C_L = 50 pF$		50	75	-	45	-	45	-	MHz
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$									
		C _L = 15 pF		120	165	-	100	-	100	-	MHz
		$C_L = 50 pF$		80	110	-	70	-	70	-	MHz
t _W	pulse width	CP HIGH or LOW; see Figure 7									
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		5.0	-	-	6.5	-	6.5	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		5.0	-	-	5.0	-	5.0	-	ns
		MR LOW; see Figure 8									
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		5.0	-	-	6.0	-	6.0	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		5.0	-	-	5.0	-	5.0	-	ns
t _{su}	set-up time	Dn to CP; see Figure 9									
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		3.0	-	-	3.0	-	3.0	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		3.0	-	-	3.0	-	3.0	-	ns
t _h	hold time	Dn to CP; see Figure 9									
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.0	-	-	1.0	-	1.0	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		1.0	-	-	1.0	-	1.0	-	ns

 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 10.

Symbol	Parameter	Conditions			25 °C		–40 °C t	o +85 °C	-40 °C to +125 °C		Unit
					Typ[1]	Max	Min	Max	Min	Max	
t _{rec}	recovery	MR to CP; see Figure 8					1	1	1		
	time	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.5	-	-	2.5	-	2.5	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		2.0	-	-	2.0	-	2.0	-	ns
C _{PD}	power dissipation capacitance	f_i = 1 MHz; V_I = GND to V_{CC}	[4]	-	14	-	-	-	-	-	pF
74AHCT	273-Q100; V _C	_C = 4.5 V to 5.5 V									
		CP to Qn; see Figure 7	[2]								
	delay	C _L = 15 pF		-	4.0	7.5	1.0	8.8	1.0	9.5	ns
		$C_L = 50 pF$		-	5.8	9.2	1.0	10.5	1.0	11.5	ns
		MR to Qn; see Figure 8	[3]								
		C _L = 15 pF		-	3.9	10.0	1.0	11.6	1.0	12.5	ns
		$C_L = 50 pF$		-	5.6	11.0	1.0	12.6	1.0	14.0	ns
f _{max}	maximum	see Figure 7									
	frequency	C _L = 15 pF		75	120	-	65	-	65	-	MHz
		$C_L = 50 pF$		50	75	-	45	-	45	-	MHz
t _W	pulse width	CP HIGH or LOW; see Figure 7		5.0	-	-	6.5	-	6.5	-	ns
		MR LOW; see Figure 8		5.0	-	-	6.0	-	6.0	-	ns
t _{su}	set-up time	Dn to CP; see Figure 9		3.0	-	-	3.0	-	3.0	-	ns
t _h	hold time	Dn to CP; see Figure 9		1.0	-	-	1.0	-	1.0	-	ns
t _{rec}	recovery time	MR to CP; see Figure 8		2.5	-	-	2.5	-	2.5	-	ns
C _{PD}	power dissipation capacitance	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$	<u>[4]</u>	-	18	-	-	-	-	-	pF

^[1] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V and V_{CC} = 5.0 V).

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}{}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}{}^2 \times f_o) \text{ where:}$

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

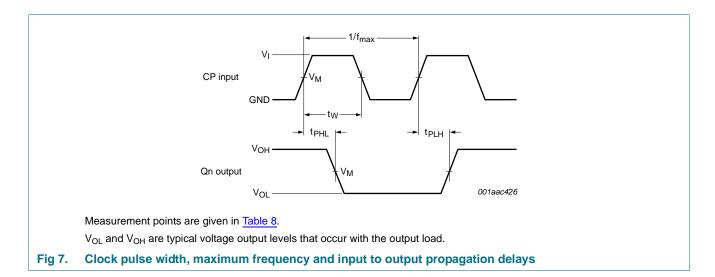
N = number of inputs switching;

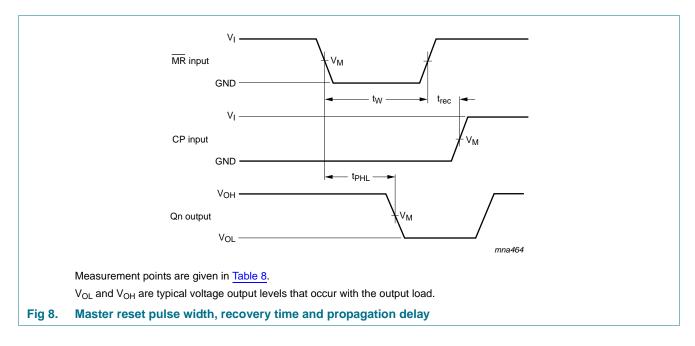
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

^[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

^[3] t_{pd} is the same as t_{PHL} only.

11. Waveforms





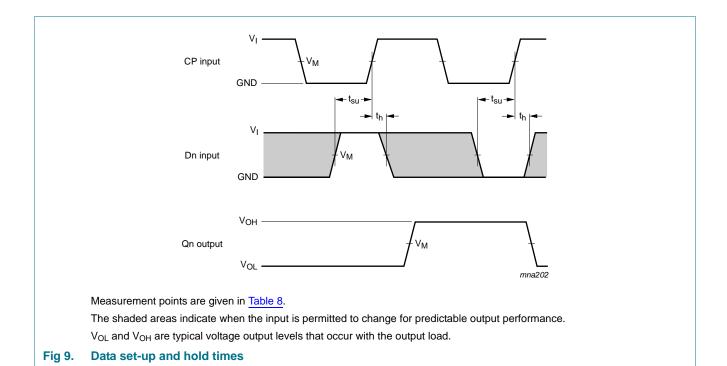
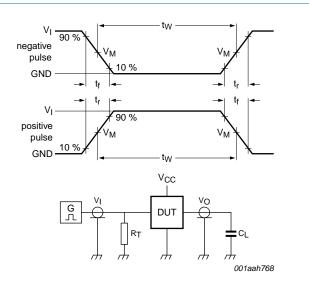


Table 8. Measurement points

Туре	Input	Output
	V _M	V _M
74AHC273-Q100	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74AHCT273-Q100	1.5 V	0.5 × V _{CC}



Test data is given in Table 9.

Definitions test circuit:

 R_T = termination resistance should be equal to output impedance Z_o of the pulse generator.

 C_L = load capacitance including jig and probe capacitance.

Fig 10. Test circuit for measuring switching times

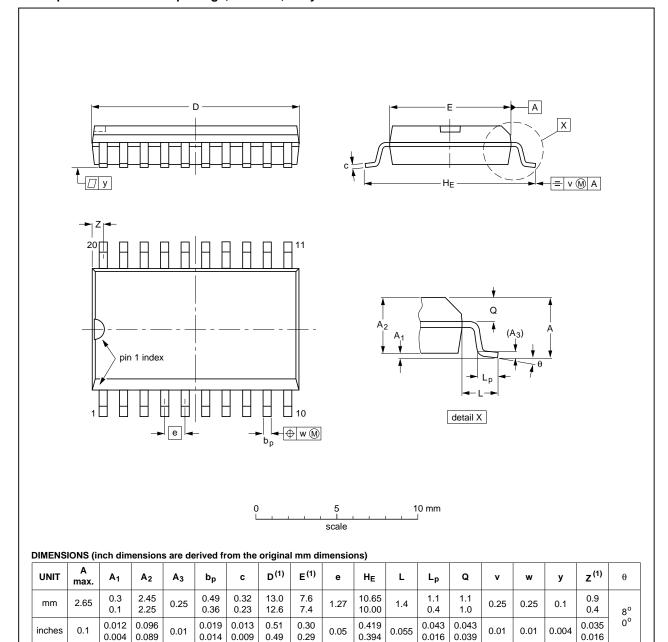
Table 9. Test data

Туре	Input Lo		Load	Test	
	VI	t _r , t _f	CL		
74AHC273-Q100	V _{CC}	≤ 3.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}	
74AHCT273-Q100	3.0 V	≤ 3.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}	

12. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1



Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

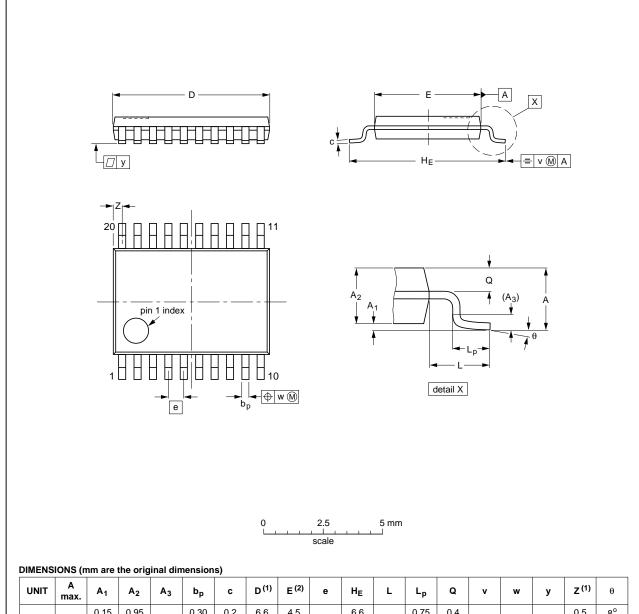
OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	1330E DATE	
SOT163-1	075E04	MS-013			99-12-27 03-02-19	

Fig 11. Package outline SOT163-1 (SO20)

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TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1



Ξ							-,												
	UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
	mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	6.6 6.4	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT360-1		MO-153				99-12-27 03-02-19	

Fig 12. Package outline SOT360-1 (TSSOP20)

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DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 x 4.5 x 0.85 mm SOT764-1

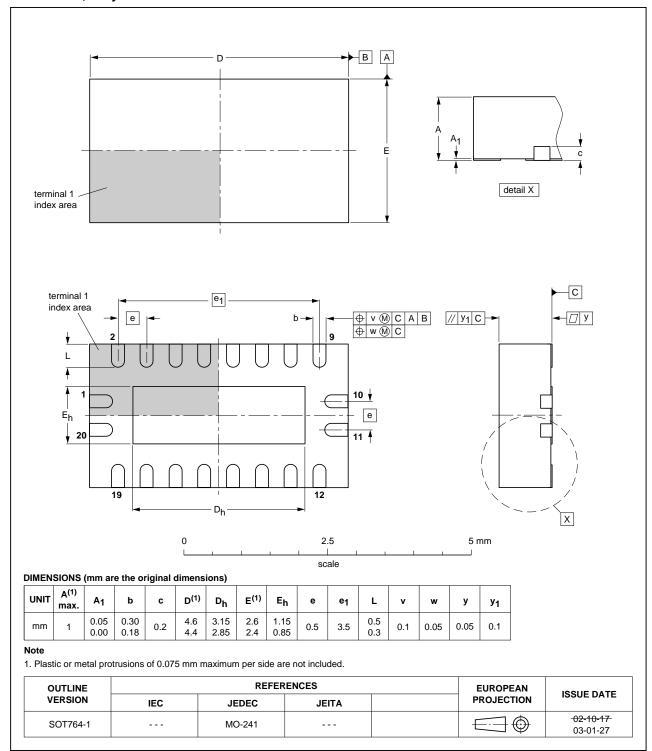


Fig 13. Package outline SOT764-1 (DHVQFN20)

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13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model
MIL	Military
MOS	Metal-Oxide Semiconductor

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT273_Q100 v.1	20130327	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition				
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.				
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.				
Product [short] data sheet	Production	This document contains the product specification.				

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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74AHC273-Q100; 74AHCT273-Q100

Octal D-type flip-flop with reset; positive-edge trigger

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17. Contents

1	General description
2	Features and benefits
3	Ordering information
4	Functional diagram
5	Pinning information
5.1	Pinning
5.2	Pin description
6	Functional description
7	Limiting values
8	Recommended operating conditions
9	Static characteristics
10	Dynamic characteristics
11	Waveforms
12	Package outline
13	Abbreviations1
14	Revision history
15	Legal information
15.1	Data sheet status 1
15.2	Definitions1
15.3	Disclaimers
15.4	Trademarks1
16	Contact information
17	Contents

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